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2. (Amended) The method of claim 1 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target with a first impurity selected from the group including [transistion] transition metals, phosphorous, and germanium.

3. (Unchanged) The method of claim 2 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target including a nickel first impurity.

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4. (Amended) The method of claim 3 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target with a first concentration of nickel in the range of 0.01 to 0.5 atomic percent (at %); and,

wherein sputter depositing a film of silicon on the substrate including a second concentration of the first impurity includes depositing a silicon film including a second concentration of nickel in the range of 0.01 to 0.5 at %.

5. (Amended) The method of claim 4 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target with a first concentration of nickel in the range of 0.05 to 0.2 at %; and,

wherein sputter depositing a film of silicon on the substrate including a second concentration of the first impurity includes depositing a silicon film including a second concentration of nickel in the range of 0.01 to 0.5 at %.

6. (Amended) The method of claim 4 wherein forming a target including silicon and a first concentration of a nickel includes forming the target

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with an additional third concentration of phosphorous less than 5×10^{17} atoms/cm³; and,

wherein sputter depositing a film of silicon on the substrate including a second concentration of nickel includes depositing a silicon film with an additional fourth concentration of phosphorous sufficient to create a first V_{th} shift in the silicon film.

7. (Unchanged) The method of claim 1 wherein sputter depositing a film of silicon on the substrate including a second concentration of the first impurity includes sputter depositing using a process selected from the group including pulsed and non-pulsed direct current (DC) sputtering.

8. (Unchanged) The method of claim 2 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target with a first concentration of germanium in the range of 5 to 30 at %; and,

wherein sputter depositing a film of silicon on the substrate including a second concentration of the first impurity includes depositing a silicon film including a second concentration of germanium in the range of 5 to 30 at %.

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9. (Amended) The method of claim 8 wherein forming a target including silicon and a first concentration of a germanium includes forming the target with an additional third concentration of phosphorous less than 5×10^{17} atoms/cm³; and,

wherein sputter depositing a film of silicon on the substrate including a second concentration of germanium includes depositing a silicon

99 film with an additional fourth concentration of phosphorous sufficient to create a first V_{th} shift in the silicon film.

10. (Unchanged) The method of claim 3 further comprising:
annealing the silicon film including the first impurity of nickel to form a silicide; and,
annealing the silicon film with the nickel silicide to crystallize the silicon film.

11. (Unchanged) The method of claim 1 wherein forming a target including silicon and a first concentration of a first impurity includes forming a target of single-crystal silicon; and,
wherein sputter depositing a film of silicon on the substrate including a second concentration of the first impurity includes forming a film of amorphous silicon.

12. (Unchanged) In the fabrication of liquid crystal displays (LCDs), a method for depositing silicon films with trace impurities, the method comprising:

supplying a substrate; and
sputter depositing silicon and a controlled amount of a first impurity on the substrate.

13. (Unchanged) The method of claim 12 further comprising:
forming a target of single-crystal silicon including a first concentration of the first impurity.

14. (Unchanged) The method of claim 12 further comprising:

following the sputter depositing, forming an amorphous silicon film including a second concentration of the first impurity overlying the substrate.

15. (Amended) The method of claim 13 wherein forming a target of single-crystal silicon including a first concentration of the first impurity includes forming a target with a first impurity selected from the group including transition metals, phosphorous, and germanium.

16. (Unchanged) The method of claim 15 wherein forming a target of single-crystal silicon including a first concentration of the first impurity includes forming a target including a nickel first impurity.

17. (Amended) The method of claim 16 wherein forming a target of single-crystal silicon including a first concentration of the first impurity includes forming a target with a first concentration of nickel in the range of 0.01 to 0.5 atomic percent (at %); and,

wherein forming an amorphous silicon film including a second concentration of the first impurity includes forming a silicon film including a second concentration of nickel in the range of 0.01 to 0.5 at %.

18. (Amended) The method of claim 17 wherein forming a target of single-crystal silicon including a first concentration of the first impurity includes forming a target with a first concentration of nickel in the range of 0.05 to 0.2 at %; and,

wherein forming an amorphous silicon film including a second concentration of the first impurity includes forming a silicon film including a second concentration of nickel in the range of 0.01 to 0.5 at %.

19. (Amended) The method of claim 17 wherein forming a target of single-crystal silicon including a first concentration of nickel includes forming a target with an additional third concentration of phosphorous less than 5×10^{17} atoms/cm³; and,

wherein forming an amorphous silicon film including a second concentration of nickel includes forming a silicon film with an additional fourth concentration of phosphorous sufficient to create a first V_{th} shift in the silicon film.

20. (Unchanged) The method of claim 12 wherein sputter depositing silicon and a controlled amount of a first impurity on the substrate includes sputter depositing using a process selected from the group including pulsed and non-pulsed direct current (DC) sputtering.

21. (Unchanged) The method of claim 15 wherein forming a target of single-crystal silicon including a first concentration of the first impurity includes forming a target with a first concentration of germanium in the range of 5 to 30 at %; and,

wherein forming an amorphous silicon film including a second concentration of the first impurity includes forming a silicon film including a second concentration of germanium in the range of 5 to 30 at %.

22. (Amended) The method of claim 21 wherein forming a target of single-crystal silicon including a first concentration of germanium includes forming a target with an additional third concentration of phosphorous less than 5×10^{17} atoms/cm³; and,

wherein forming an amorphous silicon film including a second concentration of germanium includes forming a silicon film with an additional

A12 fourth concentration of phosphorous sufficient to create a first V_{th} shift in the silicon film.

23. (Unchanged) The method of claim 16 further comprising:
annealing the silicon film including the nickel first impurity to
form a nickel silicide; and,
annealing the silicon film with the nickel silicide to crystallize the
silicon film.